

WHAT IS CLAIMED IS:

1. A wiring structure, comprising:
 - a substrate having formed thereon a first conductive layer, an insulating film formed on the first conductive layer, and a second conductive layer formed on the insulating film;
 - a conductive layer electrically coupled to the first conductive layer; and
 - a relay layer arranged below the first conductive layer and the conductive layer,
 the first conductive layer and the conductive layer being electrically coupled to each other through the relay layer.
2. The wiring structure according to Claim 1, further comprising a laminate having the first conductive layer, the insulating film, the second conductive layer, and the relay layer that are formed on a surface having a step.
3. The wiring structure according to Claim 1, the second conductive layer comprising a plurality of layers including different materials.
4. The wiring structure according to Claim 3, the second conductive layer comprising a top layer made of tungsten silicide and a bottom layer made of polysilicon.
5. The wiring structure according to Claim 1, the laminate comprising a capacitor.
6. The wiring structure according to Claim 5, the insulating film comprising a layer made of a high dielectric material.
7. The wiring structure according to Claim 6, the insulating film comprising a plurality of layers including different materials, and one of the plurality of layers being a layer made of a material having a higher dielectric constant than the other layers.
8. The wiring structure according to Claim 1, further comprising:
 - a first interlayer insulating film formed between the first conductive layer and the relay layer and between the conductive layer and the relay layer;
 - a second interlayer insulating film formed between the conductive layer and the relay layer;
 - a first contact hole that electrically couples the first conductive layer to the relay layer; and
 - a second contact hole that electrically couples the conductive layer to the relay layer.
9. A method for manufacturing a wiring structure, comprising:

forming a relay layer on a substrate;
forming a first interlayer insulating film on the relay layer;
forming in the first interlayer insulating film a first contact hole leading to the relay layer;
forming a first conductive layer on the first interlayer insulating film to bury the first contact hole;
forming an insulating film and a second conductive layer sequentially on the first conductive layer;
forming a second interlayer insulating film on the second conductive layer;
forming in the second interlayer insulating film and the first interlayer insulating film a second contact hole leading to the relay layer; and
forming a conductive layer on the second interlayer insulating film to bury the second contact hole.

10. The method for manufacturing a wiring structure according to Claim 9, the first conductive layer, the insulating film and the second conductive layer being formed on a surface having a step.

11. An electro-optical device comprising, on a substrate, data lines extending along a first direction, scanning lines extending along a second direction intersecting the data lines, and pixel electrodes and thin film transistors arranged to correspond to intersection regions between the data lines and the scanning lines, the electro-optical device further comprising:

storage capacitors that are electrically coupled to the thin film transistors and the pixel electrodes; and

relay electrodes that are arranged below the pixel electrodes and the storage capacitors, respectively,

one electrode of a pair of electrodes constituting each storage capacitor being electrically coupled to the pixel electrode through the relay electrode.

12. The electro-optical device according to Claim 11, the storage capacitor being formed on a surface having a step.

13. The electro-optical device according to Claim 11, the one electrode being a pixel-potential-side capacitor electrode electrically coupled to the pixel electrode and the thin film transistor,

the storage capacitor comprising the pixel-potential-side capacitor electrode, a fixed-potential-side capacitor electrode arranged to face the pixel-potential-side capacitor

electrode and having a fixed potential, and a dielectric film interposed between the pixel-potential-side capacitor electrode and the fixed-potential-side capacitor electrode; and
the dielectric film comprising a laminate including a layer made of a high dielectric material.

14. The electro-optical device according to Claim 11, the relay electrodes being formed using a same material as the gate electrodes of the thin film transistors included in the scanning lines.

15. The electro-optical device according to Claim 11, the fixed-potential-side capacitor electrode being formed to cover the pixel-potential-side capacitor electrode.

16. An electronic apparatus utilizing an electro-optical device according to Claim 11.